

**Silicon Diffused Power Transistor**

**BUX87-1100**

**GENERAL DESCRIPTION**

High voltage, high speed, low capacitance npn power transistor in a SOT78 envelope intended for use in the dynamic focus circuit of televisions and monitors.

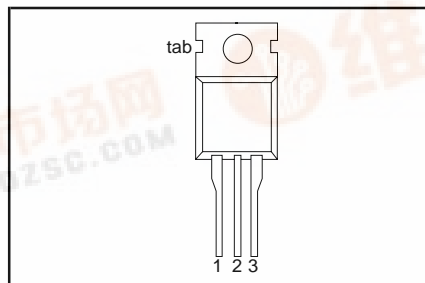
**QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1100	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	700	V
$I_C$	Collector current (DC)		-	0.5	A
$I_{CM}$	Collector current peak value		-	1	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	46	W

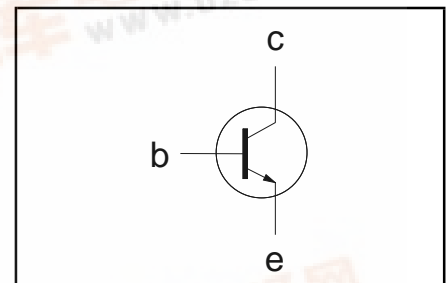
**PINNING - TO220AB**

PIN	DESCRIPTION
1	emitter
2	collector
3	base
tab	collector

**PIN CONFIGURATION**



**SYMBOL**



**LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1100	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	700	V
$I_C$	Collector current (DC)		-	0.5	A
$I_{CM}$	Collector current (peak value) $t_p = 2\text{ ms}$		-	1	A
$I_B$	Base current (DC)		-	0.2	A
$I_{BM}$	Base current (peak value)		-	0.3	A
$-I_{BM}$	Reverse base current (peak value) <sup>1</sup>		-	0.3	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	46	W
$T_{stg}$	Storage temperature		-40	150	$^\circ\text{C}$
$T_j$	Junction temperature		-	150	$^\circ\text{C}$

**THERMAL RESISTANCES**

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base		-	2.7	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	60	-	K/W

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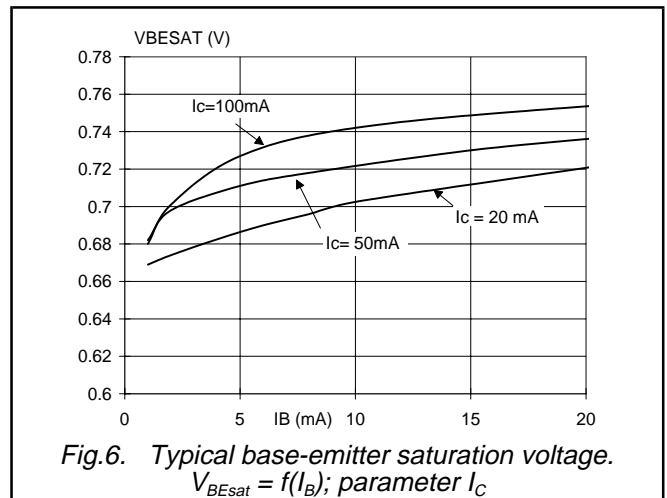
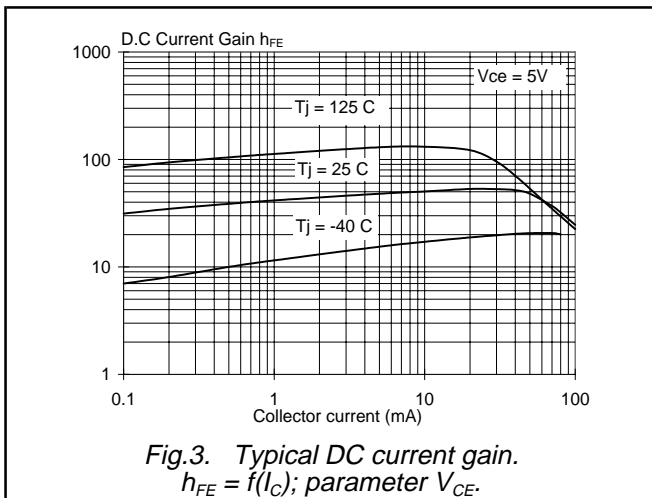
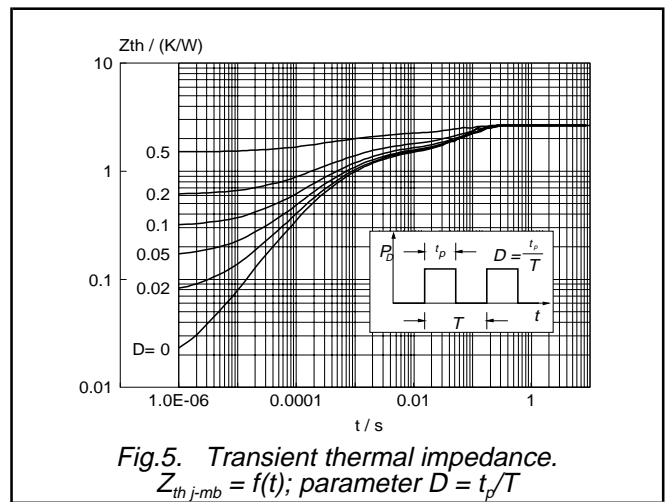
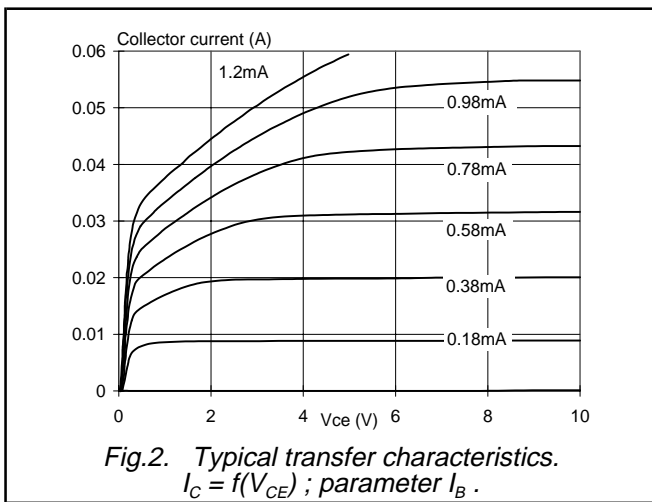
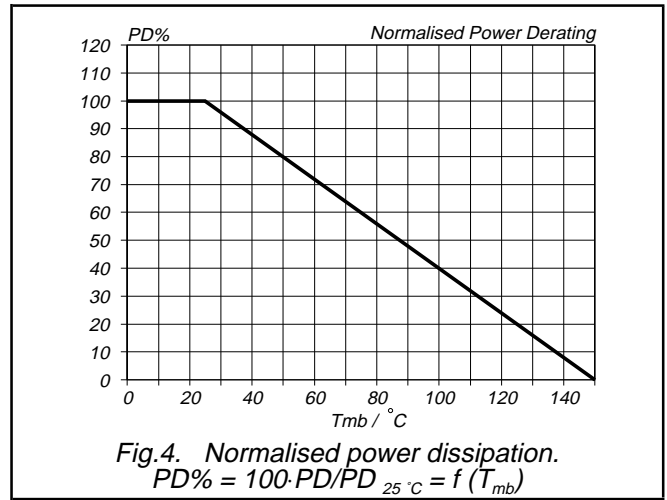
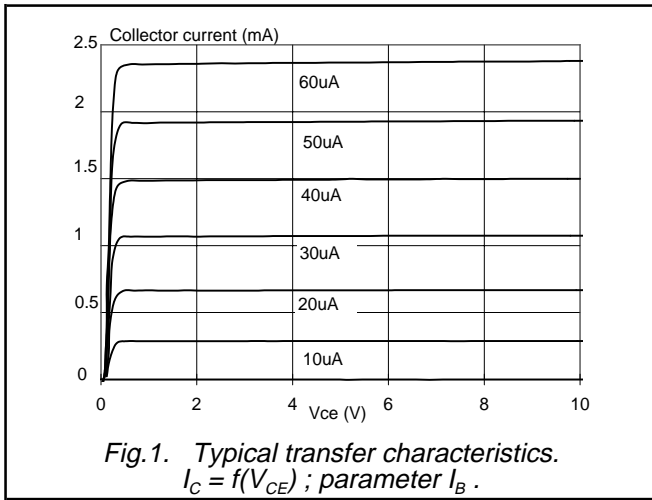
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**ELECTRICAL CHARACTERISTICS** $T_{mb} = 25\text{ °C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	100	$\mu\text{A}$
$I_{CES}$		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ °C}$	-	-	1.0	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	1	mA
$h_{FE}$	DC current gain	$I_C = 50\text{ mA}; V_{CE} = 5\text{ V}$	26	50	125	
$h_{FE}$	DC current gain	$I_C = 20\text{ mA}; V_{CE} = 5\text{ V}$	26	50	150	
$C_{ob}$	Output capacitance	$V_{CB} = 100\text{ V}; f = 1\text{ MHz}$	-	4.7	-	pF

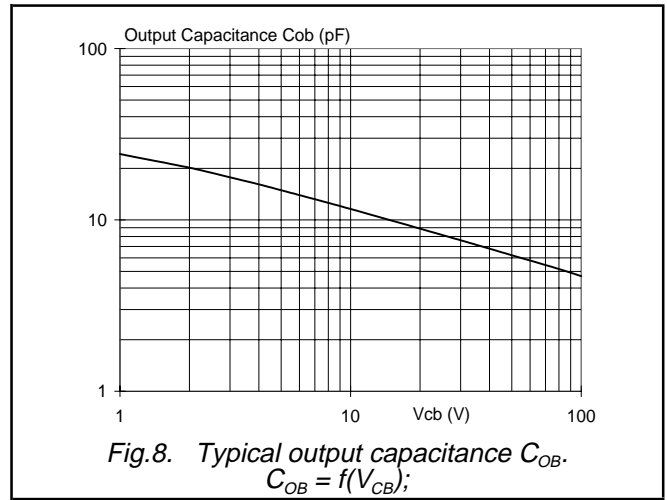
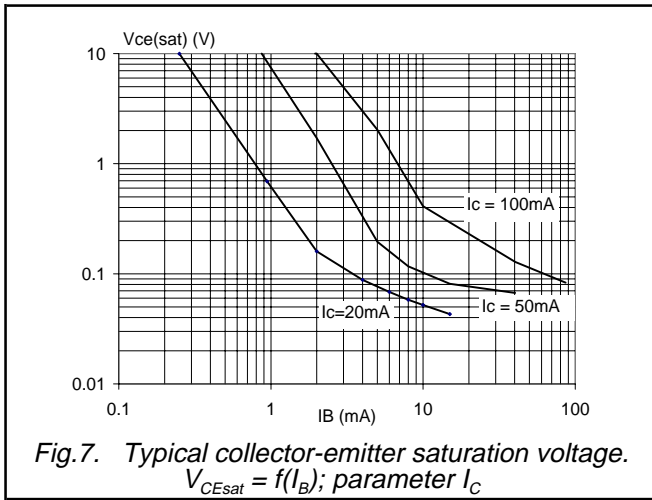
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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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